

## BAT54STB

### SCHOTTKY BARRIER (DUAL) DIODES

#### DESCRIPTION

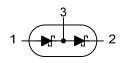
Planar Schottky barrier diodes are encapsulated in the SOT-523 small plastic SMD package. Single diodes and dual diodes with different pin configuration are available.

#### FEATURES

- \* Low forward voltage
- \* Guard ring protected
- \* Small plastic SMD package

SOT-523

#### SYMBOL



#### ORDERING INFORMATION

Ordering Number		Deekere	Pin Assignment			Deeking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BAT54STBL-AN3-R	BAT54STBG-AN3-R	SOT-523	A1	K2	K1A2	Tape Reel	
Note: Pin Assignment: A: Anode K: Cathode							

BAT54STB <u>G</u> - <u>AN3</u> -Ŗ		
	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AN3: SOT-523
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

#### MARKING



#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
PER DIODE				
Continuous Reverse Voltage	V <sub>R</sub>	30	V	
Continuous Forward Current	l <sub>F</sub>	200	mA	
Repetitive Peak Forward Current (t <sub>P</sub> <1s, δ≤0.5)	I <sub>FRM</sub>	300	mA	
Non-repetitive Peak Forward Current (t <sub>P</sub> <10ms)	I <sub>FSM</sub>	600	mA	
Junction Temperature	TJ	+125	°C	
Storage Temperature	T <sub>STG</sub>	-60 ~ +150	°C	
PER DEVICE				
Power Dissipation (T <sub>A</sub> ≤25°C)	PD	230	mW	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ <sub>JA</sub>	500	°C/W	

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	V <sub>F</sub>	I <sub>F</sub> = 0.1mA			240	mV
		I <sub>F</sub> = 1mA			320	mV
Forward Voltage (See Fig.1)		I <sub>F</sub> = 10mA			400	mV
		I <sub>F</sub> = 30mA			500	mV
		I <sub>F</sub> = 100mA			800	mV
Reverse Current (See Fig.2)	I <sub>R</sub>	V <sub>R</sub> = 25V			2	μA
Reverse Recovery Time (see Fig.4)	t <sub>rr</sub>	When switched from I <sub>F</sub> =10mA to I <sub>R</sub> = 10mA, R <sub>L</sub> = 100 $\Omega$ measured at I <sub>R</sub> = 1mA			5	ns
Diode Capacitance (see Fig.3)	CD	f = 1 MHz, V <sub>R</sub> = 1V;			10	рF



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### TYPICAL CHARACTERISTICS

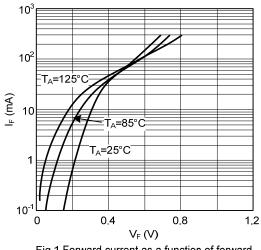


Fig.1 Forward current as a function of forward voltage; typical values.

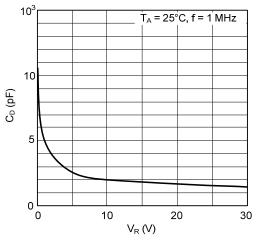
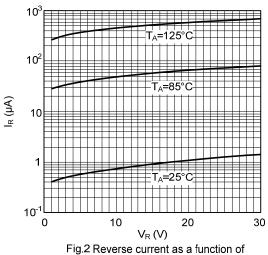


Fig.3 Diode capacitance as a function of reverse voltage; typical values.



reverse voltage; typical values.

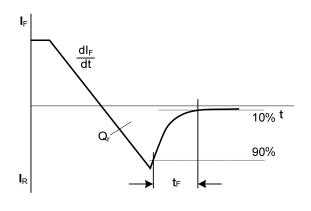


Fig.4 Reverse recovery definitions

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